BC807-16LT1, BC807-25LT1, BC807-40LT1

General Purpose Transistors

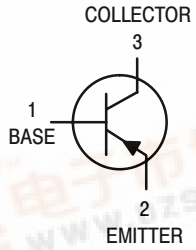
PNP Silicon

ON Semiconductor®

http://onsemi.com

Features

- Pb−Free Packages are Available



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V_{CEO}	−45	V
Collector - Base Voltage	V_{CBO}	−50	V
Emitter - Base Voltage	V_{EBO}	−5.0	V
Collector Current − Continuous	I_C	−500	mAdc

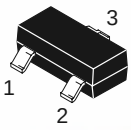
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

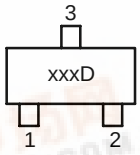
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR−5 Board, (Note 1) T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T_J, T_{stg}	−55 to +150	°C

1. FR−5 = 1.0 x 0.75 x 0.062 in.
2. Alumina = 0.4 x 0.3 x 0.024 in 99.5% alumina.

MARKING DIAGRAM



SOT−23
CASE 318
STYLE 6



xxx = 5A (BC807−16LT1)
5B1 (BC807−25LT1)
5C (BC807−40LT1)
D = Date Code

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector−Emitter Breakdown Voltage (I_C = −10 mA)		$V_{(BR)CEO}$	−45	−	−	V
Collector−Emitter Breakdown Voltage (V_{EB} = 0, I_C = −10 μA)		$V_{(BR)CES}$	−50	−	−	V
Emitter−Base Breakdown Voltage (I_E = −1.0 μA)		$V_{(BR)EBO}$	−5.0	−	−	V
Collector Cutoff Current		I_{CBO}				
(V_{CB} = −20 V)			−	−	−100	nA
(V_{CB} = −20 V, T_J = 150°C)			−	−	−5.0	μA
ON CHARACTERISTICS						
DC Current Gain		h_{FE}				−
(I_C = −100 mA, V_{CE} = −1.0 V)	BC807−16		100	−	250	
	BC807−25		160	−	400	
	BC807−40		250	−	600	
(I_C = −500 mA, V_{CE} = −1.0 V)			40	−	−	
Collector−Emitter Saturation Voltage (I_C = −500 mA, I_B = −50 mA)		$V_{CE(sat)}$	−	−	−0.7	V
Base−Emitter On Voltage (I_C = −500 mA, I_B = −1.0 V)		$V_{BE(on)}$	−	−	−1.2	V
SMALL−SIGNAL CHARACTERISTICS						
Current−Gain − Bandwidth Product (I_C = −10 mA, V_{CE} = −5.0 Vdc, f = 100 MHz)		f_T	100	−	−	MHz
Output Capacitance (V_{CB} = −10 V, f = 1.0 MHz)		C_{obo}	−	10	−0.7	pF

DEVICE ORDERING INFORMATION

Device	Package	Shipping†
BC807−16LT1	SOT−23	3,000 Tape & Reel
BC807−16LT3	SOT−23	10,000 Tape & Reel
BC807−25LT1	SOT−23	3,000 Tape & Reel
BC807−25LT1G	SOT−23 (Pb−Free)	
BC807−25LT3	SOT−23	10,000 Tape & Reel
BC807−40LT1	SOT−23	3,000 Tape & Reel
BC807−40LT1G	SOT−23 (Pb−Free)	
BC807−40LT3	SOT−23	10,000 Tape & Reel
BC807−40LT3G	SOT−23 (Pb−Free)	

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

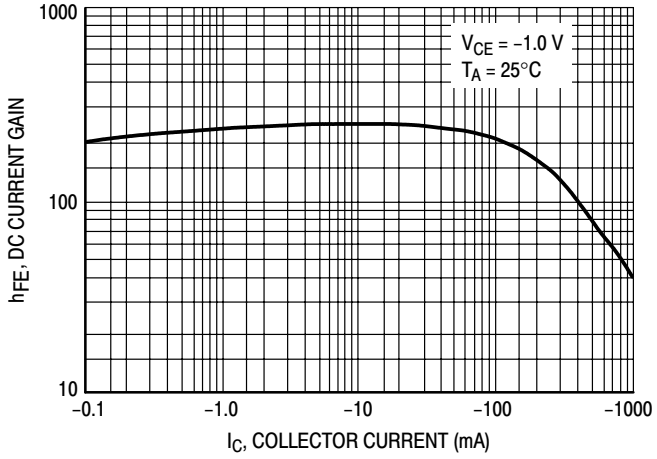


Figure 1. DC Current Gain

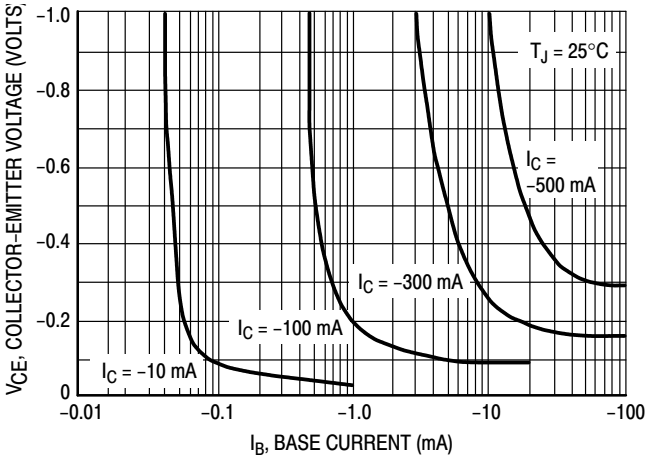


Figure 2. Saturation Region

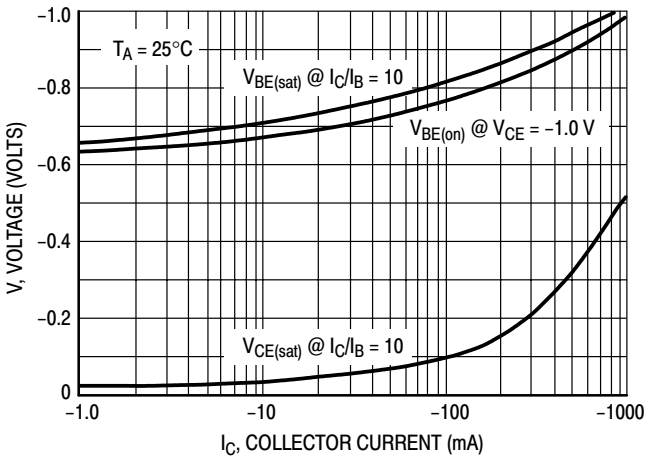


Figure 3. “On” Voltages

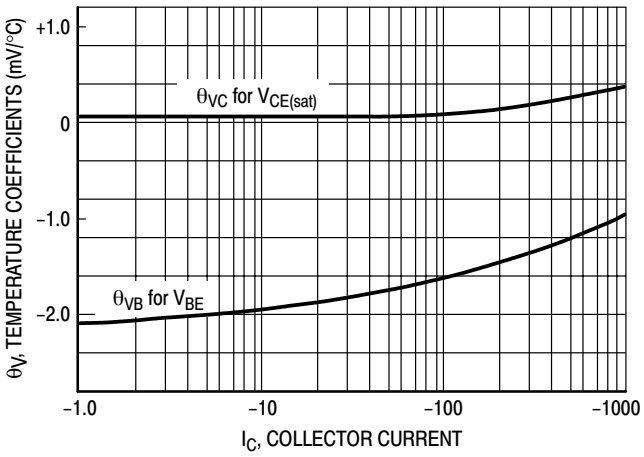


Figure 4. Temperature Coefficients

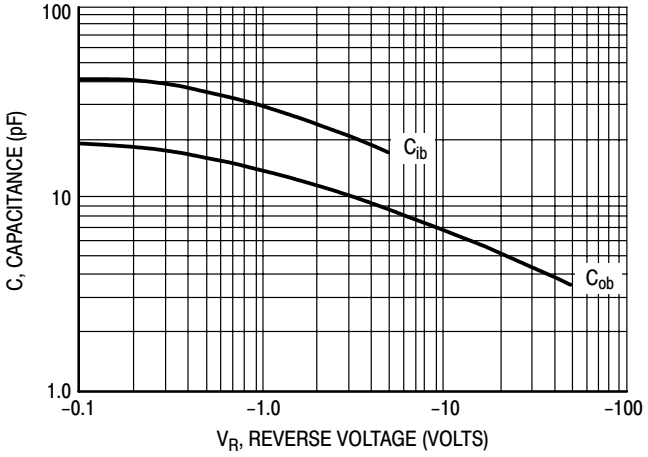
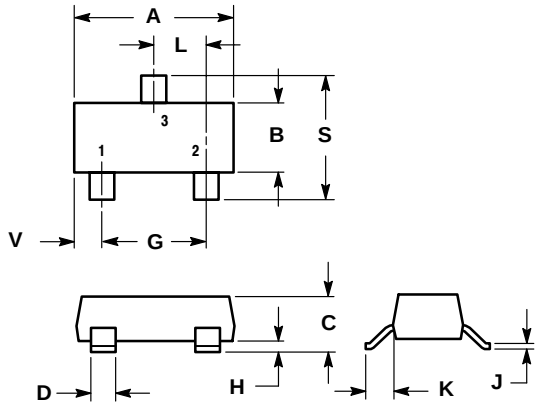


Figure 5. Capacitances

PACKAGE DIMENSIONS

SOT−23 (TO−236)
CASE 318−09
ISSUE AI

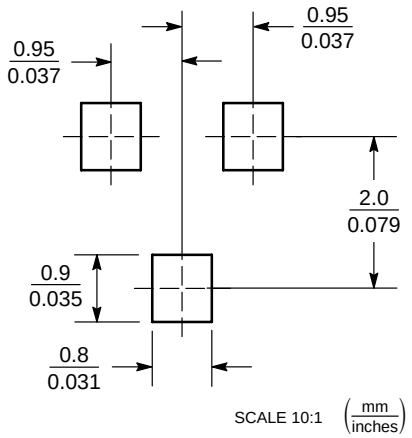


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318−01, −02, AND −06 OBSOLETE, NEW STANDARD 318−09.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0385	0.0498	0.99	1.26
D	0.0140	0.0200	0.36	0.50
G	0.0670	0.0826	1.70	2.10
H	0.0040	0.0098	0.10	0.25
J	0.0034	0.0070	0.085	0.177
K	0.0180	0.0236	0.45	0.60
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.0984	2.10	2.50
V	0.0177	0.0236	0.45	0.60

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center
2−9−1 Kamimeguro, Meguro−ku, Tokyo, Japan 153−0051
Phone: 81−3−5773−3850

ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative.